PROC, 15TH INT. CONF. PHYSICS OF SEMICONDUCTORS, KYOTO, 1980 J. PHYS. SOC. JAPAN **49** (1980) SUPPL. A p. 741–744

MAGNETOOPTICAL INVESTIGATION OF THE BANDSTRUCTURE OF $Pb_{1-x}Ge_xTe$ AT THE STRUCTURAL PHASE TRANSITION ($0_h \rightarrow C_{3v}$)

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The influence of the structural phase transition in PbGeTe on the electronic bandstructure has been studied by interband-magnetooptical transitions above and below T_{C} . The observed transition energies are explained by an extended Mitchell and Wallis $\vec{k} \cdot \vec{p}$ scheme taking into account strain and displacement effects.

I. Introduction

Pb1-xGexTe exhibits a structural phase transition from the cubic O_h to a low temperature rhombohedral C_{3V} structure [1]. Apart from changes in lattice dynamics [2,3] this phase transition manifests itself in a modification of the electronic bandstructure: the four equivalent conduction and valenceband valleys at the L-point of the Brillouinzone in the cubic phase are split into three equivalent L-states (triplet) and a T-state (singlet) below the phase transition temperature T_C[4-7]. Below T_c a relative displacement u (order parameter) of the group IV and VI lattice sites along an <111> direction occurs and simultaneously rhombohedral shear and dilatational strains appear.

II. Theory

The bandstructure change due to the 0_h-C_{3v} transition is taken into account by considering the strain and displacement effects. For the calculation of the magnetic levels in the cubic phase the Mitchell and Wallis (MW) scheme [8,9] is used. Below Tc the strain-effects cause relatively small shifts of the band-gaps (different at L- and T-points of the BZ) and according to the procedure of Takaoka [6] and Nishi-kawa [7,1] the effect of the relative displacement u is considered by calculating the matrix elements for $(\nabla V)\vec{u} = u_+(\nabla V)_- + u_-(\nabla V)_+ + u_Z(\nabla V)_Z$ for the singlet (T) valley $(\vec{u} = u(0,0,1), u_Z = u, u_{\pm} = 0)$ and the triplet (L) valleys $(u_Z = -(u/3)z, u_{\pm} = 2u/3 (x + iy)$ and taking them into account in the MW scheme by using the MW wavefunctions for the L61 + (α,β) and L62 - (α,β) levels. This results in an additional matrix Hamiltonian:

 $H' = \begin{bmatrix} 0 & 0 & iM_{1}u & 0 \\ 0 & 0 & 0 & -iM_{1}u \\ -iM_{1}u & 0 & 0 & 0 \\ 0 & iM_{1}u & 0 & 0 \end{bmatrix} H' = \begin{bmatrix} 0 & 0 & -iM_{1}u/3 & i2\sqrt{2}M_{t}u/3 \\ 0 & 0 & i2\sqrt{2}M_{t}u/3 & iM_{1}u/3 \\ iM_{1}u/3 & -i2\sqrt{2}M_{t}u/3 & 0 & 0 \\ -i2\sqrt{2}M_{t}u/3 & -iM_{1}u/3 & 0 & 0 \end{bmatrix}$

 $\rm M_1$ and $\rm M_t$ are the longitudinal and transverse optical deformation potential matrix elements. The effect of the relative displacement u is taken into account only in the two-band CB-VB interaction and its effect on the four distant levels is neglected.

For a magnetic field \vec{B} ||c, the Landau-states of the singlet (T) are then given by the eigenvalues of:



Since the lowest Landau-state of the CB and the highest of the VB are determined in their magnetic field dependence only by the remote band contributions, these two Landau-states do not reflect the influence of u. For the triplet state a complication arises due to the fact that the Landau-states are coupled (n : no good quantum number) and no longer a 4x4 scheme leads to the magnetic quantum states. By solving a 12x12 matrix approximate solutions for the first three Landau levels in CB and VB were obtained.

III.Experimental



Fig. 1 Transmission vs B for $T>T_C$ and $T<T_C$ of $Pb_{1-x}Ge_xTe$ for $\vec{B}||$ surface normal (cubic [111])

Epitaxially grown n- and p-type Pb1-xGexTe films (D = 5...20 jum) were produced by the hot-wall technique on {111} BaF2 substrates. Interband magnetooptical transmission experiments (σ_+, σ_-) were performed with CO-laser lines (189 to 246.6 meV), in magnetic fields up to 6.5 T in Faraday configuration $\vec{B} ||\vec{k}||$ surface normal ([111]). For samples with Gecompositions between 0.6 % and 1.33 % and carrier-concentrations between 7x1016 and 3x10¹⁷ cm⁻³ the transition temperature varied between 10 and 45 K. Figure (1) shows typical experimental transmission data as a function of B for various temperatures. Above T_C (42K) the shift of the equivalent transmission extrema is determined by $E_g(T)$. In addition the splitting between σ_+ and σ_- transitions is small and comparable to PbTe. Below T_c the transitions exhibit a clear splitting between the two circular polarisations.

In Fig. (2) the apparent temperature dependence of several magnetooptical transitions indicated by their resonance field B is plotted. A typical bend occurs near $T_{\rm C}$ which clearly distinguishes a region of a rather rapid change of B with T from a nearly constant transition energy region, which reflects the temperature dependence of the energy gaps at L-and T-point near $T_{\rm C}$.



Fig. 2 Resonance B-positions for several transitions for $T^{>}<T_{C}$ IV. Discussion

The comparison of the experimental and calculated transmission data for the cubic phase is based on the 4x4 scheme, using the selection rules $\Delta n=0$ and $\Delta \sigma=\pm 1$ for RCP, LCP radiation in Faraday configuration. In Fig. (3) this comparison is shown for n-PbGeTe (1%) and a temperature of 53 K. Transitions between the Landau ladders of the valleys oriented ||B and within the Landau ladder system of the valleys oriented oblique to \overline{B} are observed.

Below T_{C} a relative shift of the singlet (T) and triplet (L) states arises, which is of the order of some meV for Ge contents of 1%. In the CB and the VB the T-states are shifted upwards relative to the L-states. Therefore transitions between triplet states

may be blocked, depending on the position of the Fermi-energy. An additional complication arises from the existence of domains with c-axis not only || to the surface normal but also inclined to it |2,5| (c'|| <111>).





Below T_c, the Landau-states are qualitatively different from the ones in the cubic phase, and up- and downstates (with respect to ± Mju) occur.

In Fig. (4) experimental data for $T < T_C$ are compared with calculated transition energies for singlet states, oblique singlet states (in c'-domains), triplet states in c- and c'-domains. A short-coming of the present fit is the assumption that u influences only the twoband interaction, which leads to an artifact in the O CB and VB Landau states, which are not bent by the M_1u terms. For the triplet states the interband transitions occur not at kz=0 but at finite k (depending on Mju). The parameters used are shown in Table I (MW notation [9]). Despite the obvious simplifications, this model describes also observed intraband transitions.

Acknowledgement

This work was supported by the Fonds zur Förderung der wiss. Forschung, Austria and by the Deutsche Forschungsgemeinschaft. Numerical calculations were done at the Rechenzentrum der Universität Würzburg.



Interband transitions in Fig. 4 $Pb_{1-x}Ge_{x}Te$ below T_{c} for $\sigma_{+}(o)$ and $\sigma_{-}(x)$ involving singlet (T) and triplet (L) states of the c (||surface normal) and the c' (oblique to surface normal)-domains: Calculated data: (---), (---) (---) for singlet- and triplet states. $0 \downarrow$, $\dagger \rightarrow 0 \uparrow$, \downarrow transitions were corrected for the influence of u on O↓ CB-and VB-Landau states

Table I Band parameters o	$f Pb_{1}$, Ge, Te (x = 0	0.01)
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	two band	far band parameters
T > T _C	Eg=0.2114 eV	$m_t^+/m_0^{=-0.073}, m_t^-/m_0^{=0.077}, m_1^+/m_t^{=11.2}$
(T=53 K)	$2P_{L}^{2}/m_{0}=5.52 \text{ eV}$	mī/mī=8.7; g1=1.1, gī=-2.8
	$P_{\perp}^{2}/P_{\parallel}^{2}=14.4$	gī/gī=2.95, g†/g‡=3.35
T < T _c	E _g =0.204 eV (T)	
(T=35 K)	2P ₁ /m _o =5.5 eV P ₁ ² /P ₁ ² =14.4 M ₁ u=M _t u=0.022 eV	as above

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